Semiconductor Wafers - FG for optimum edge retention

1160

Grinding

	Steps	PG	FG
Surface	Type	SiC Foil #500	MD-Largo
	Disc speed (rpm)	300	150
Abrasive	Type		DP-Susp. P 9 µm
	Predosing/dosing		3/6
Lubricant	Type	Water	DP-Blue
	Predosing/dosing		3/6
	Force (N)	25	30
	Holder direction	>>	>>
	Holder speed (rpm)	150	150
	Time (min)	1	6

Polishing

	Steps	DP	DP 2	OP
Surface	Type	MD-Dur	MD-Dur	MD-Chem
	Disc speed (rpm)	150	150	150
Abrasive	Type	DP-Susp. P 3 µm	DP-Susp. P 1 µm	OP-S, 0.25 µm
	Predosing/dosing	3/6	3/6	1/10
Lubricant	Type	DP-Blue	DP-Blue	
	Predosing/dosing	3/10	3/10	
	Force (N)	25	20	10
	Holder direction	>>	>>	><
	Holder speed (rpm)	150	150	150
	Time (min)	5	5	2

Method comments

The method is developed to fit a standard equipment configuration with 30 mm specimen on 300mm disc. Dosing levels are valid for following equipment: Tegramin, AbraPol and LaboPol

For advice on how to adjust the method to fit your equipment, please take a look at Preparation Parameters.

The preparation time for the plane grinding (PG) step depends very much on the condition of the samples and if they are prepared as single specimens or clamped in a specimen holder. Please check the samples after the first step and repeat it if necessary.

Take a look at Preparation Parameters